

# IEEE SW Test Workshop

Semiconductor Wafer Test Workshop



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FEINMETALL

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## Contact formation in wafer test probing

Fritting, breakdown, pad damage and conduction



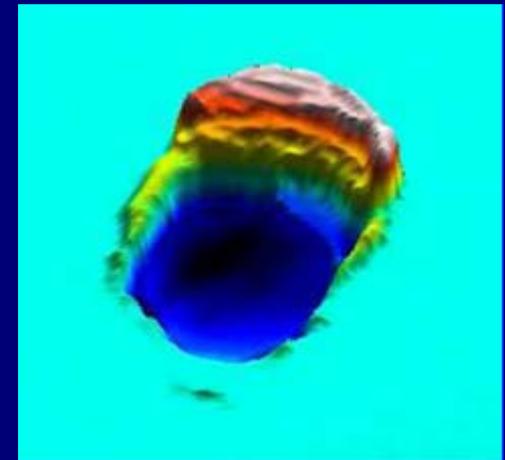
June 12 to 15, 2011  
San Diego, CA USA

# Our motivation for these experiments:

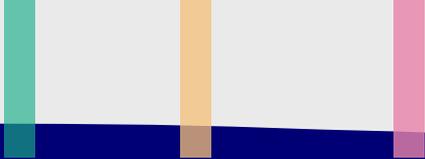
Today's probing is rather aggressive: 200-800nm probe mark depth is common practice.

**POAA** requires very careful probing to avoid damaging the delicate structures under the pad.

- We want to probe less aggressively!
- We need to understand the contact interface!



scrub mark on Al



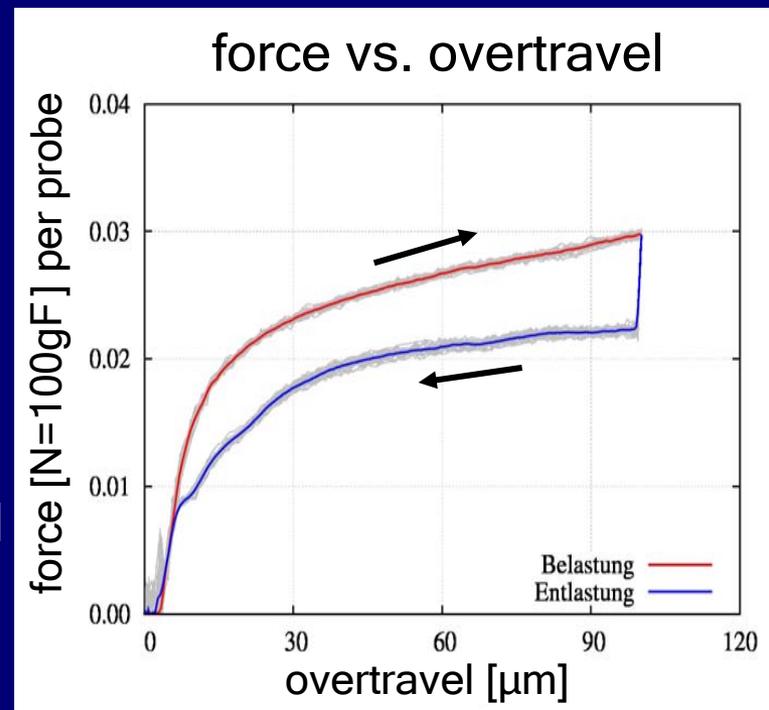
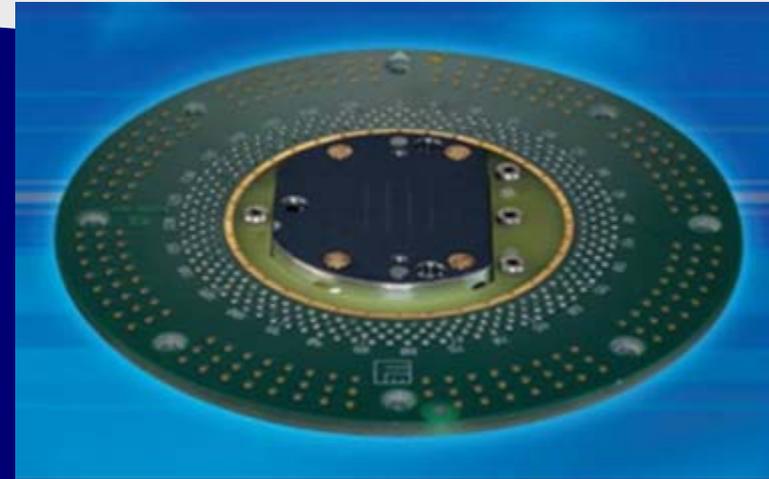
# Content

- System description: Test machines, methods and material.
- Results for probing copper, aluminum and gold.
- Influence of fritting.
- Properties of a very soft contact.
- Simulation as a tool to optimized soft contacts.

# System Description

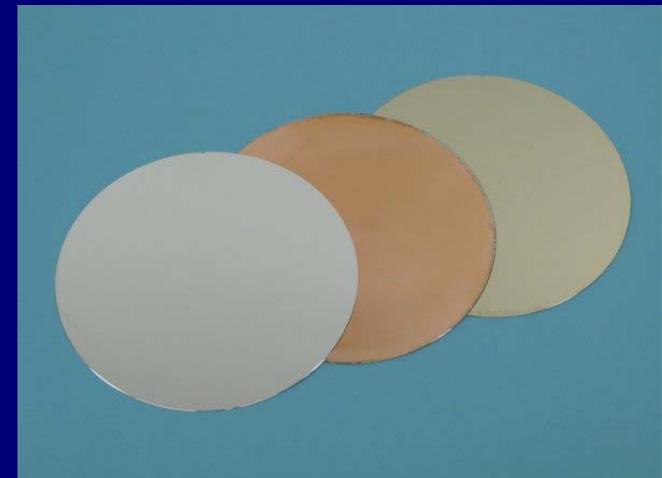
- ViProbe® S-Type  
59μm pitch for up to 180°C  
self scrub vertical probe technology
- Trivar®-HC probe for high current
- 45 probes test image  
(more than 2000 probes possible)

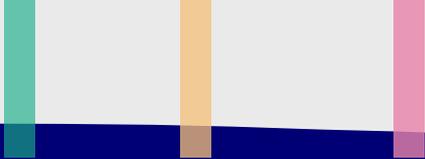
→ all tests done using this type of probe head



# System Description

- Prober: UF-3000
- Tester: Keithley 2601A  
with 500-channel multiplexer
- Class 10.000 clean room
- Wafer:
  - blank AlCu<sub>0.5%</sub>, 1200nm
  - blank plated Cu, 7100nm
  - blank plated Au, 2000nm



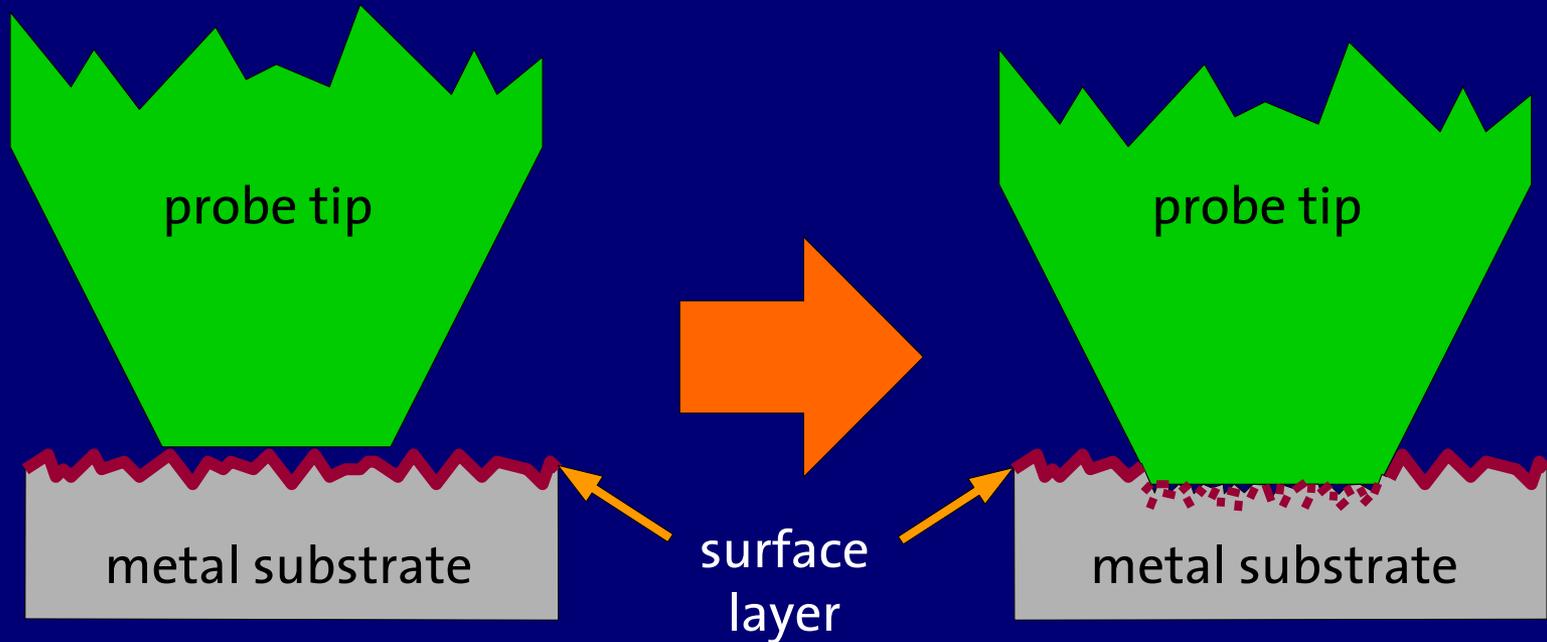


We know we can  
**probe perfectly**

.... but to learn we need to  
**provoke failure!**

- NO online cleaning
- reduced overtravel for some tests
- mixing pad materials

# Classical Concept of an Electrical Contact

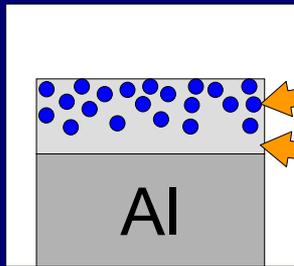


a non conductive surface film  
inhibits current to flow

metal has partly contact to tip  
fritting\* widens the contact areas

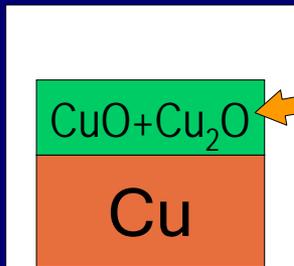
\* see SWTW, MARTENS 2006 and 2009 and DEGEN 2006

# Aluminum, Copper, Gold - Surfaces

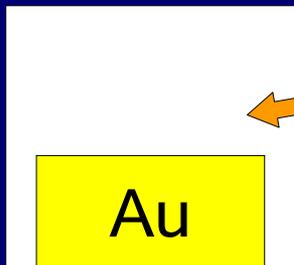


>17nm  $\text{Al}_2\text{O}_3 + \text{H}_2\text{O}$

>3 nm  $\text{Al}_2\text{O}_3$



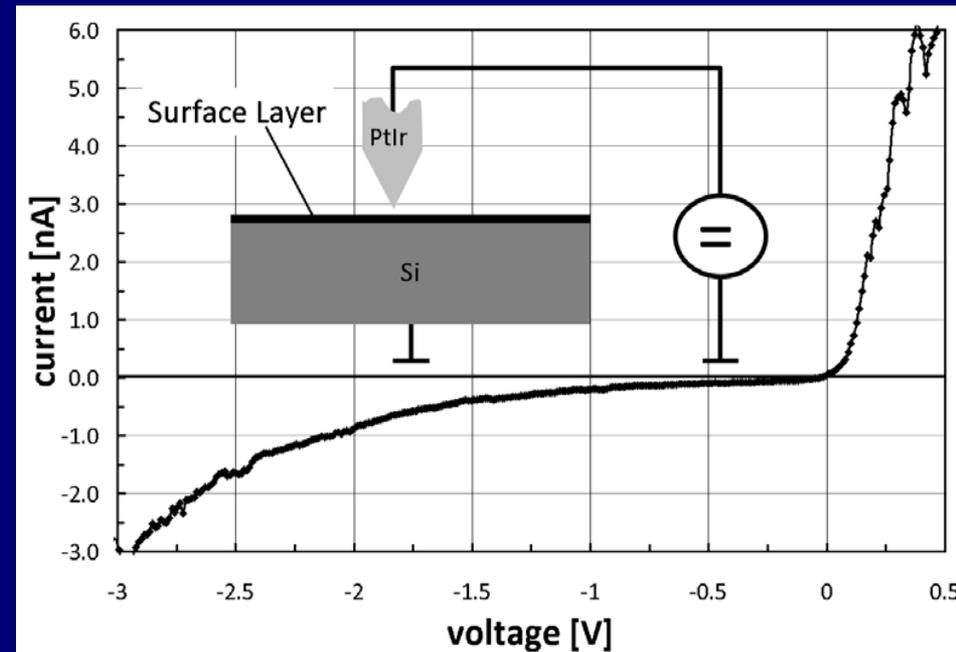
>20nm  $\text{Cu}_x\text{O}_y$



no film

dimensions  
are examples

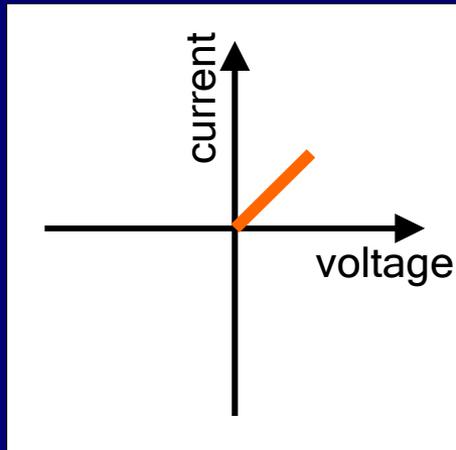
Non-metal surface layers have  
non linear I / U properties  
(probed by STS measurement)



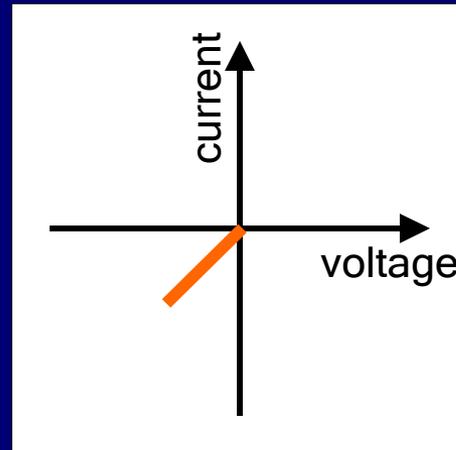
If the film is closed  
we should see an energy gap.

# Experiment setup

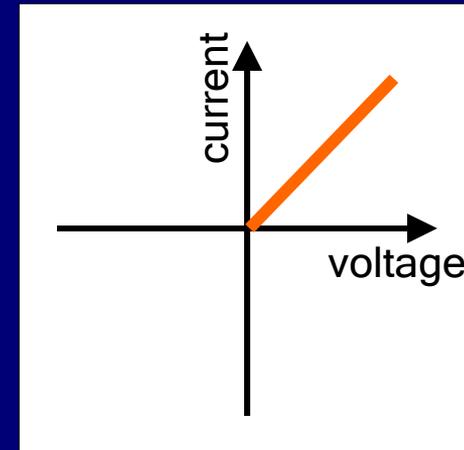
- Common probing (+28°C; +180°C, 80μm overtravel) with common resistance testing @ 2V, 20mA limits
- for selected touchdowns alternatively "I / U -measurements", 6x current slopes with limited voltages:  
10μA to 100mA (6steps/dec.)  
@ +10mV; -10mV; +100mV; -100mV; +1.0V; -1.0V



1st: +10mV



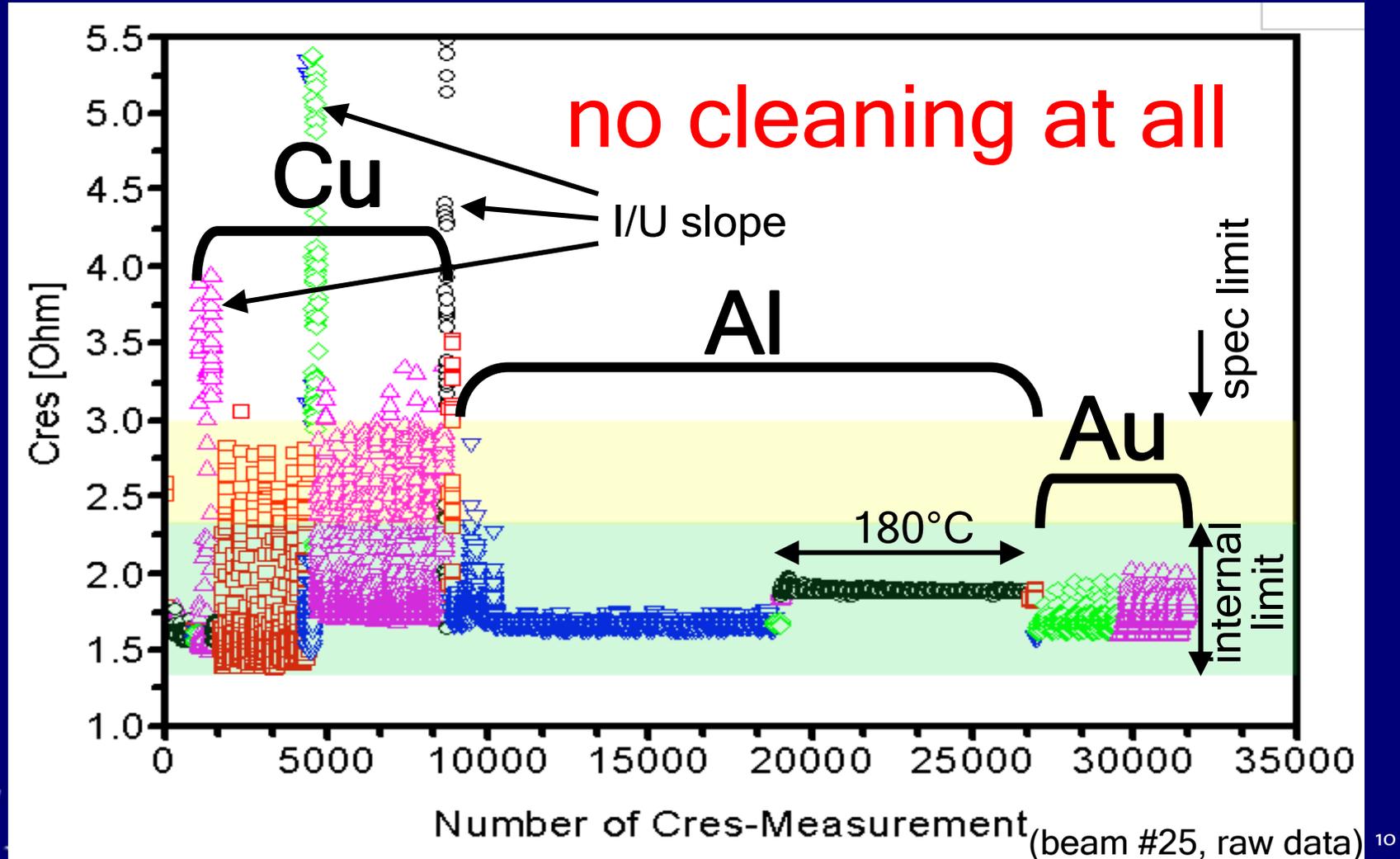
2nd: -10mV



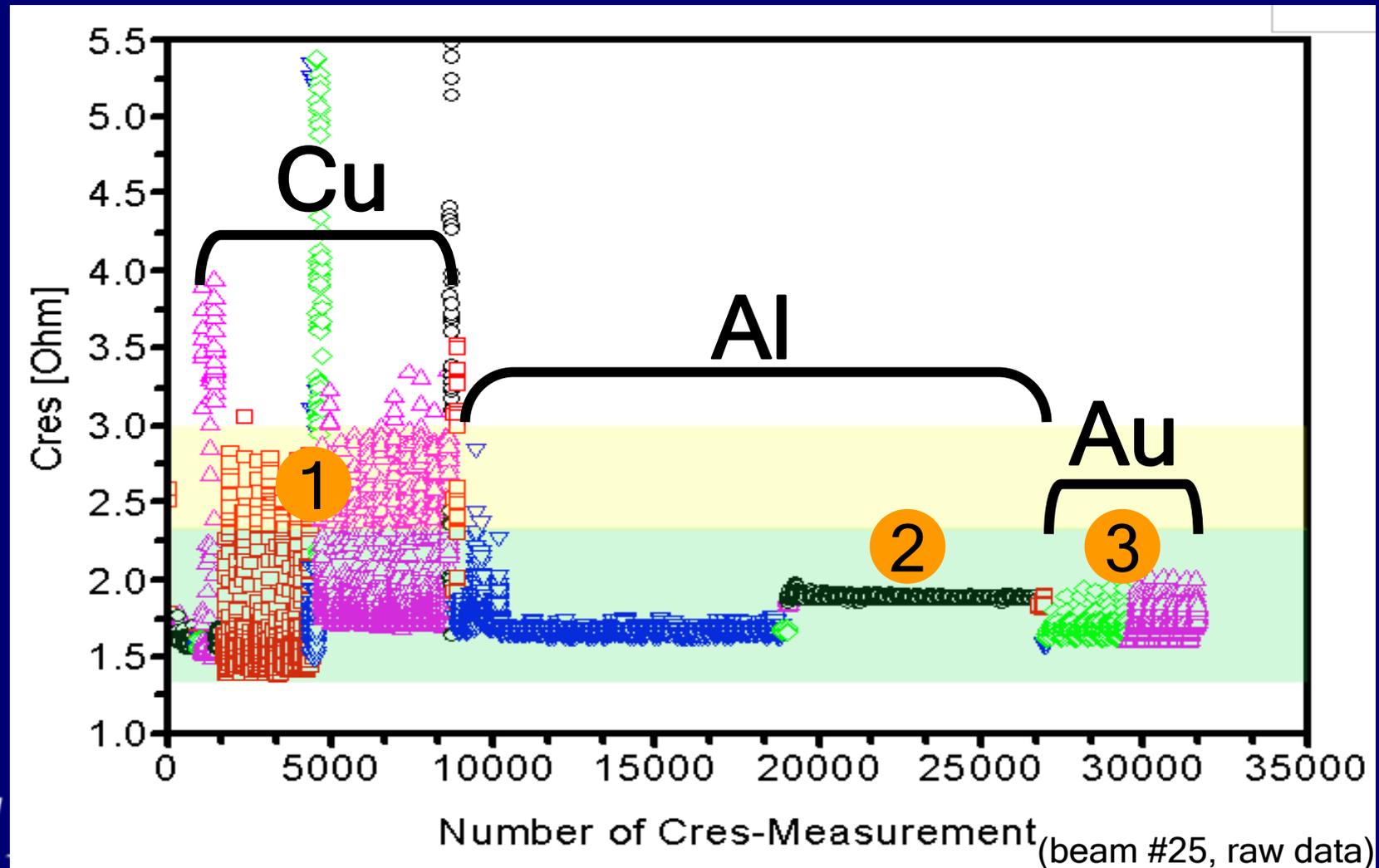
3rd: +100mV

....

# Experiment Overview: 26 single steps

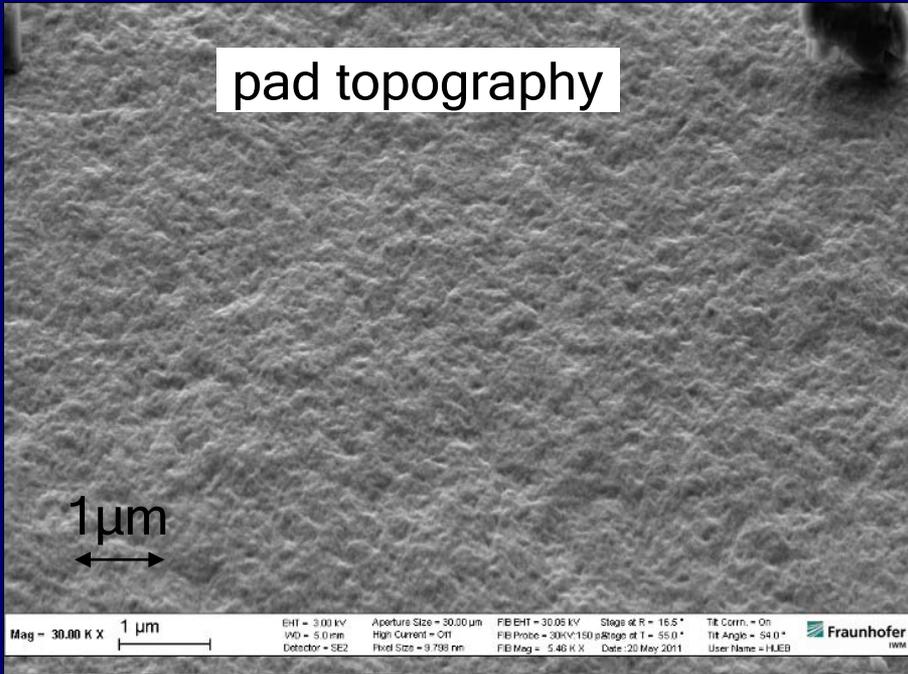


# Experiment Overview: reference



# 1 Cu Probing: Material

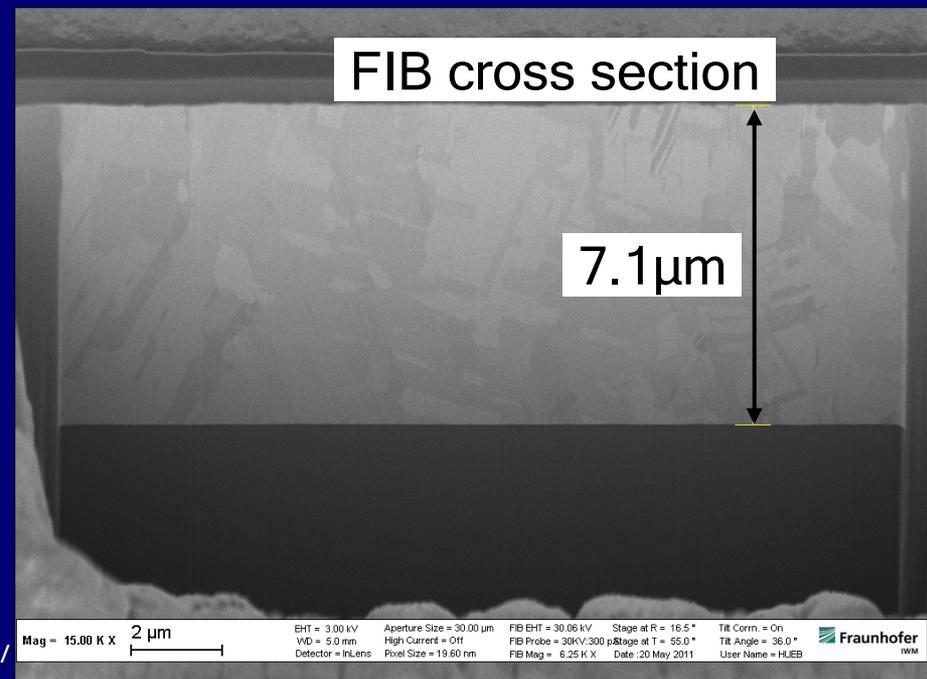
pad topography



scrub mark



FIB cross section



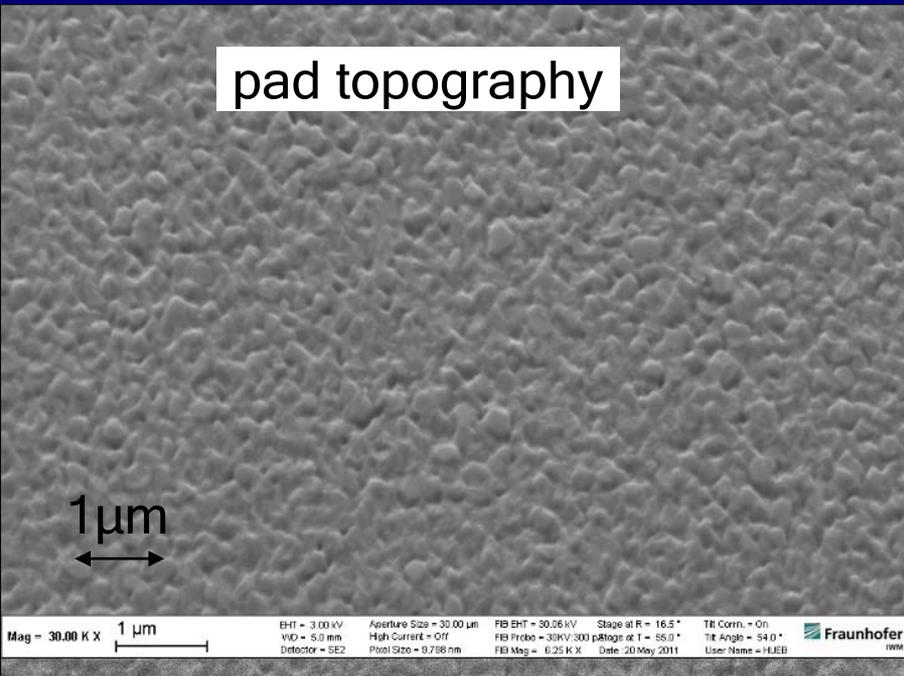
Modulus<sup>1)</sup>: 120 GPa  
 Hardness<sup>1)</sup>: 1.42 GPa  
 Resistance:  $1.93 \cdot 10^{-8}$  Ohm\*m

<sup>1)</sup>by nano-indentation



## 2 Al-Probing: Material

pad topography



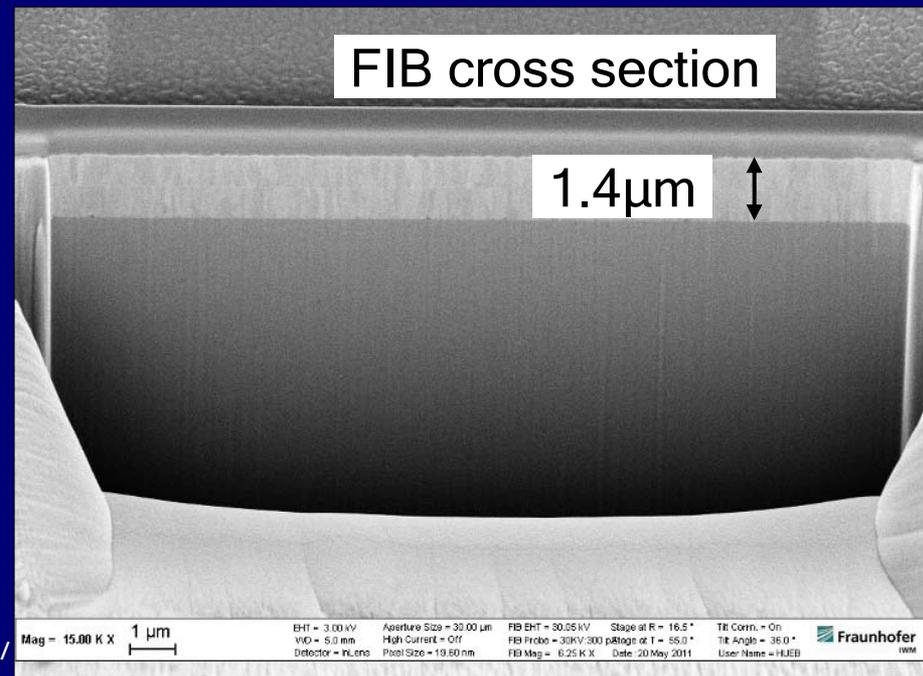
Modulus<sup>1)</sup>: 75 GPa  
Hardness<sup>1)</sup>: 1.75 GPa  
Resistance:  $3.51 \cdot 10^{-8}$  Ohm\*m

<sup>1)</sup>by nano-indentation

scrub mark

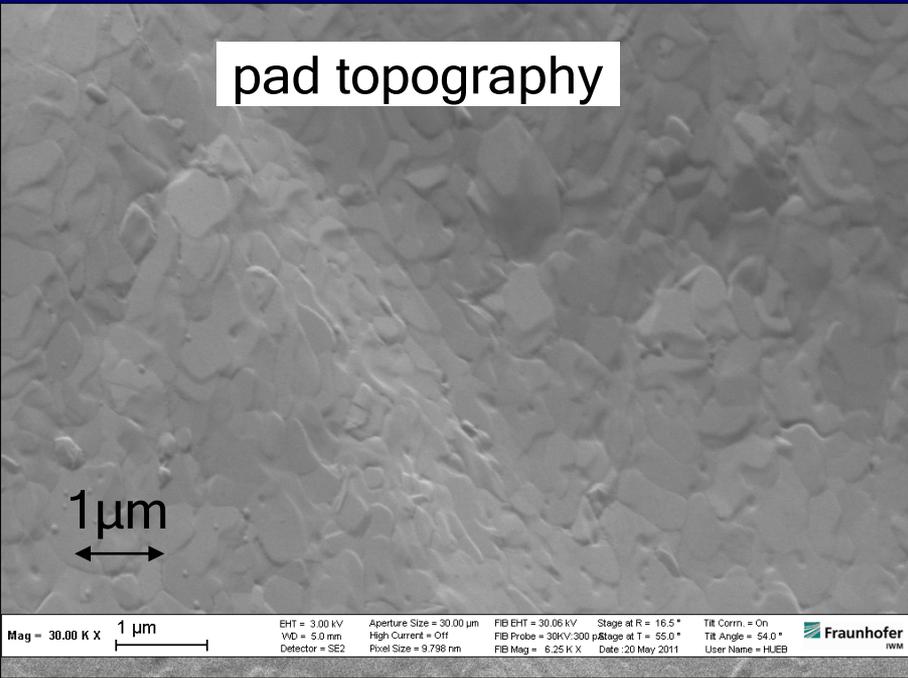


FIB cross section



# 3 Au-Probing: Material

pad topography



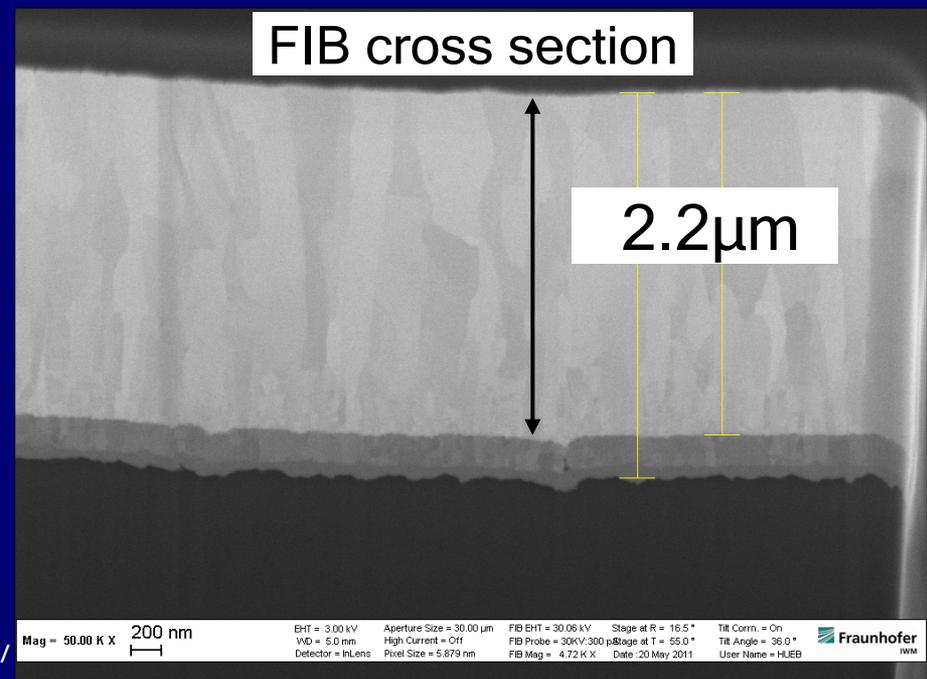
Modulus<sup>1)</sup>: 83 GPa  
 Hardness<sup>1)</sup>: 0.99 GPa  
 Resistance:  $2.98 \cdot 10^{-8} \text{ Ohm} \cdot \text{m}$

<sup>1)</sup>by nano-indentation

scrub mark

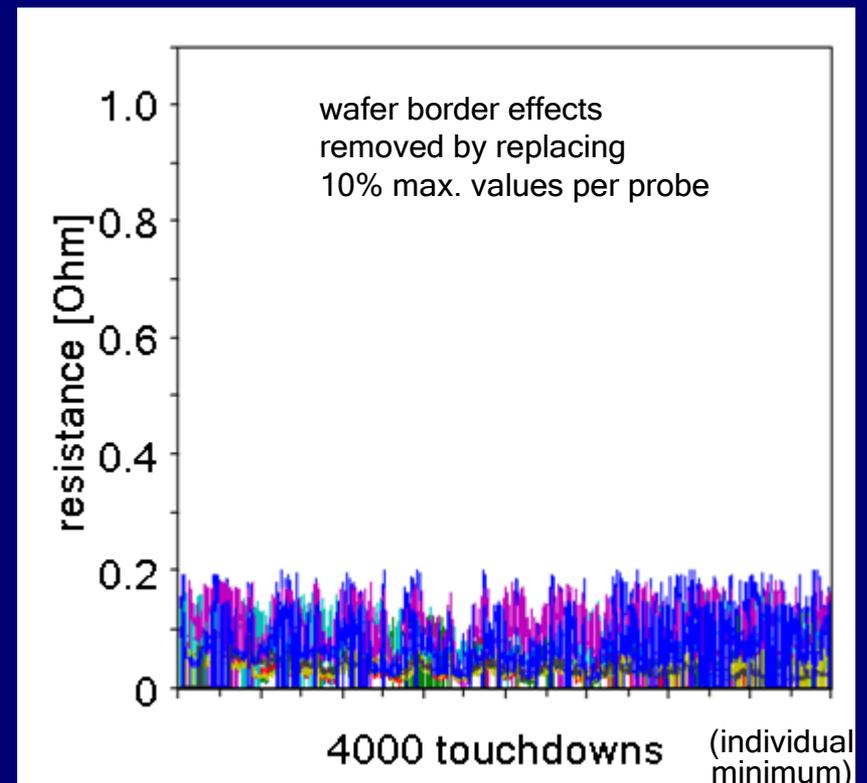
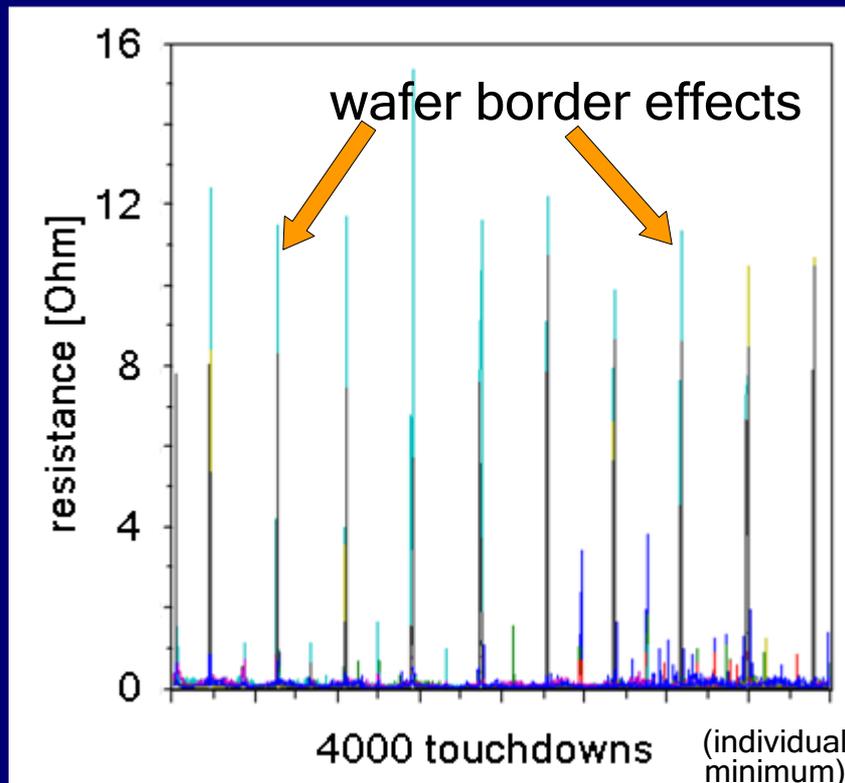


FIB cross section



# 1 Copper Probing: Cres

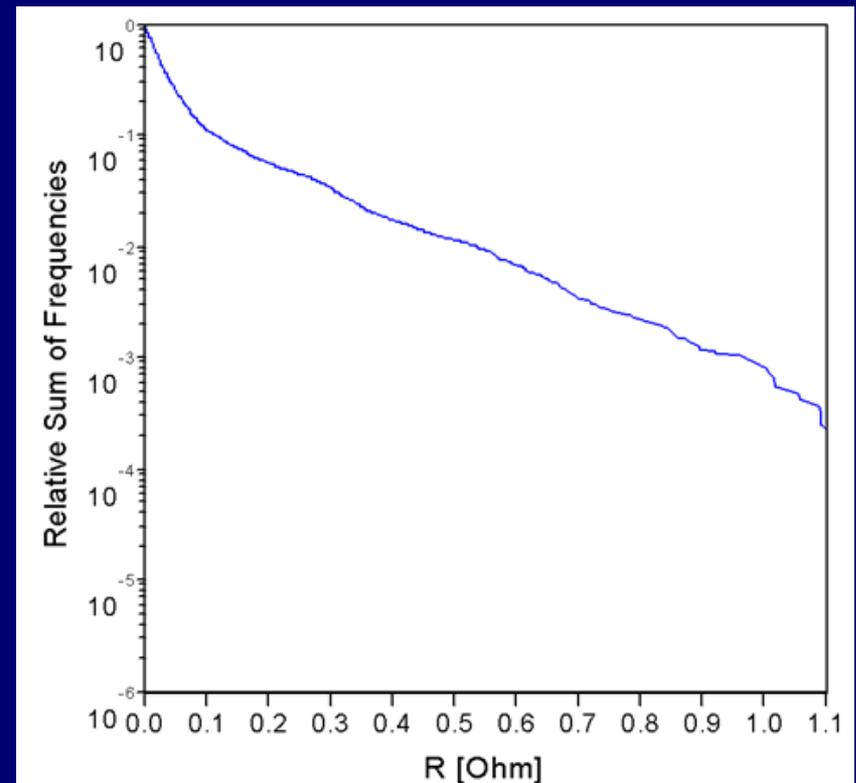
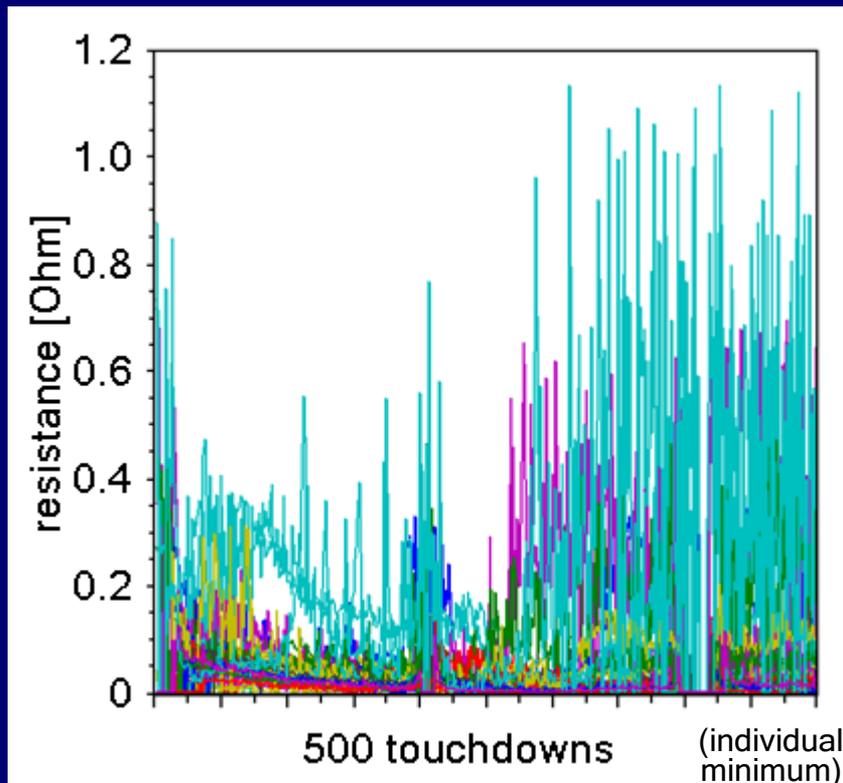
Best performing probes only (8 out of 45)



→ the system reacts sensitive to disturbances

# 1 Copper Probing: Cres

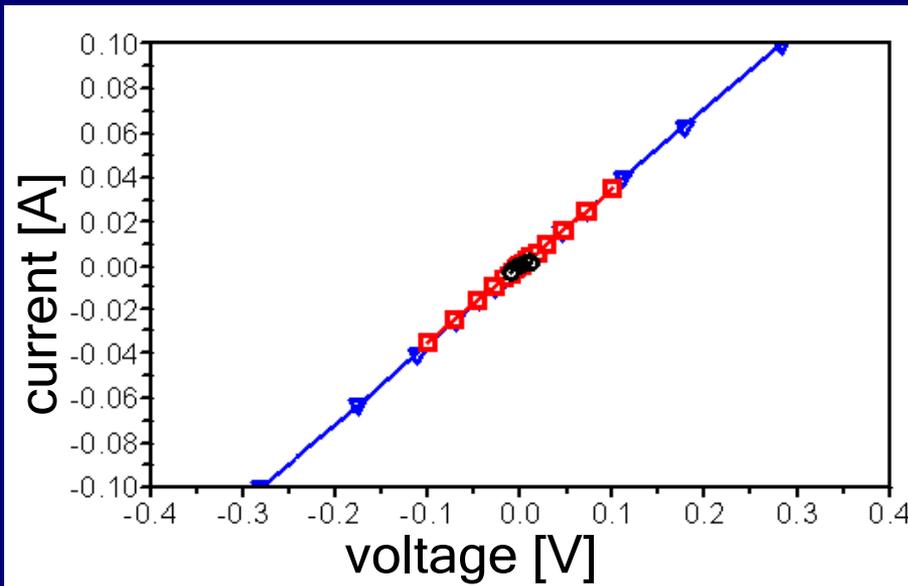
Best performing probes only (33 out of 45, wafer border effects removed)



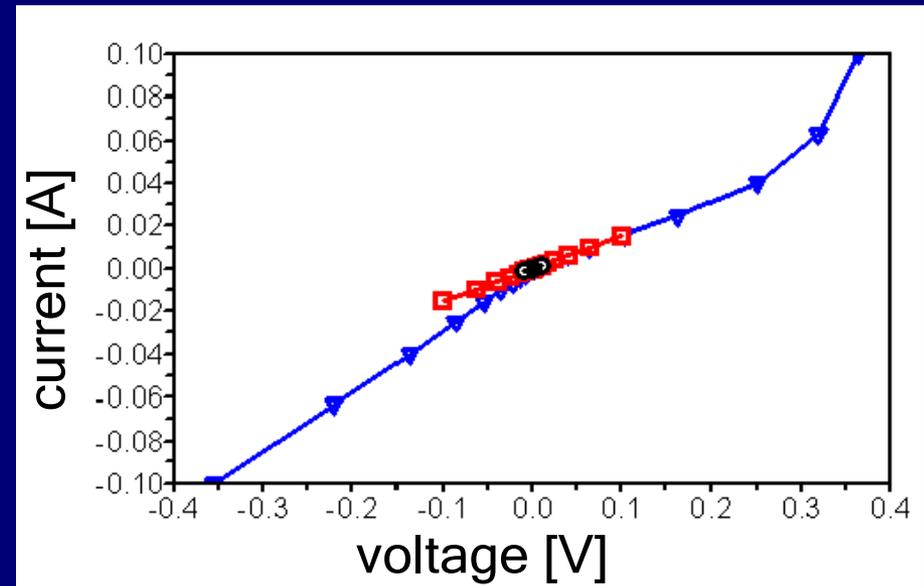
→ 2/3 are in spec initially

# 1 Copper Probing: fritting

selected probes



Example for bad contact on copper: 2.8 Ohm

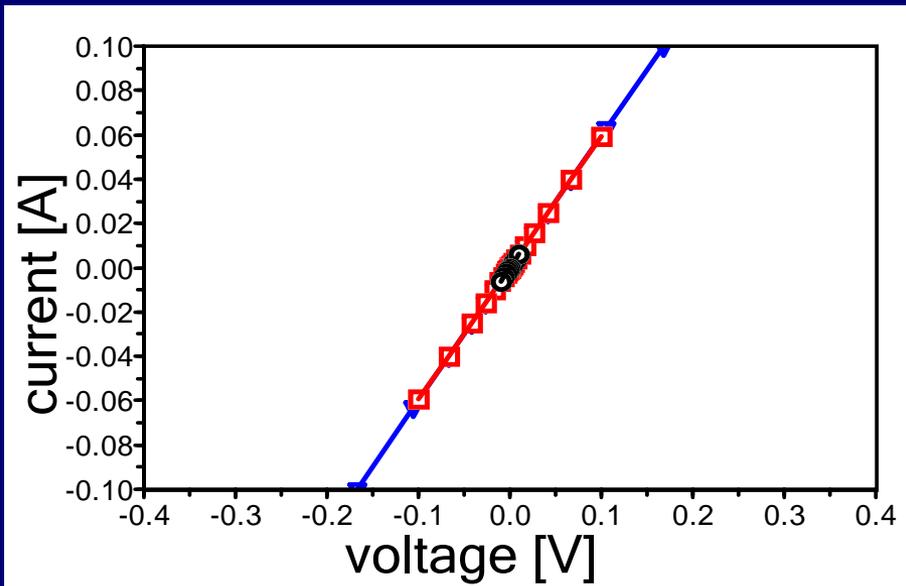


Same probe, next touchdown.  
Starting with even worse resistance of 6.3 Ohm,  
fritting at 0.35V, then 3.5 Ohm resistance.

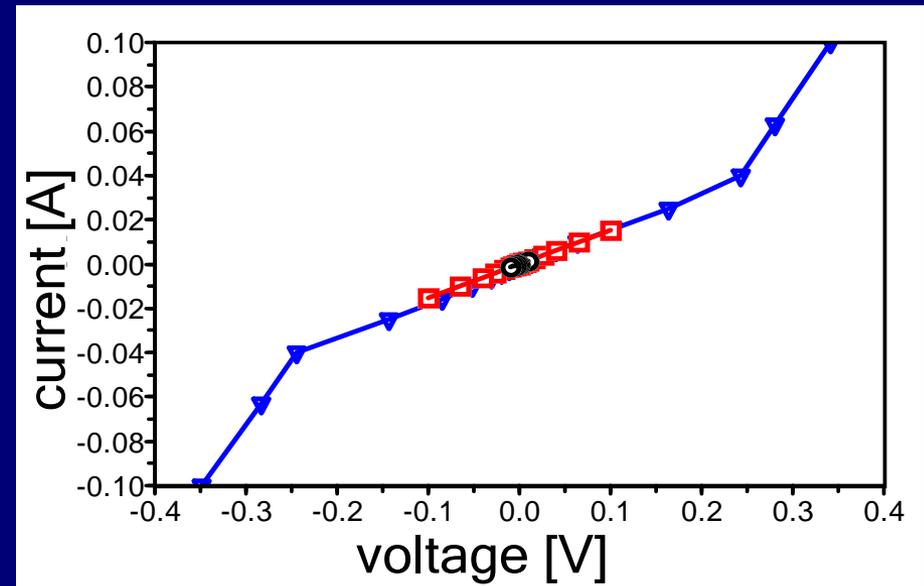
→ fritting makes it better, but not perfect

# 1 Copper Probing: I / U measurements

selected probes



Example for a good contact on copper: 1.7 Ohm



Example for a contact that shows an energy barrier around +/- 0.25V

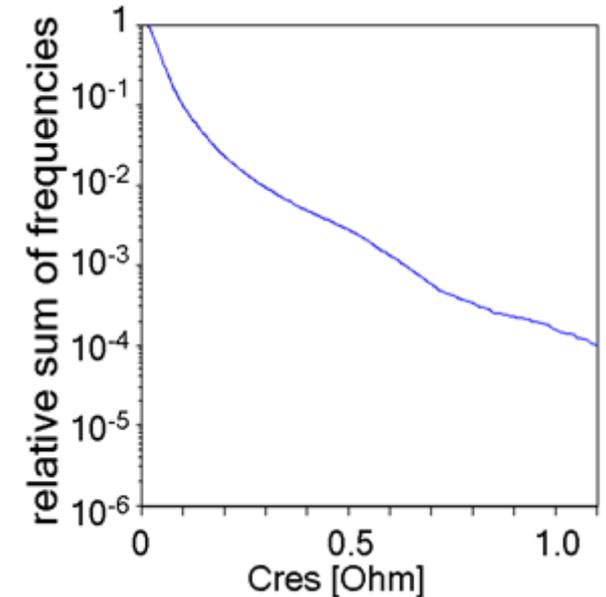
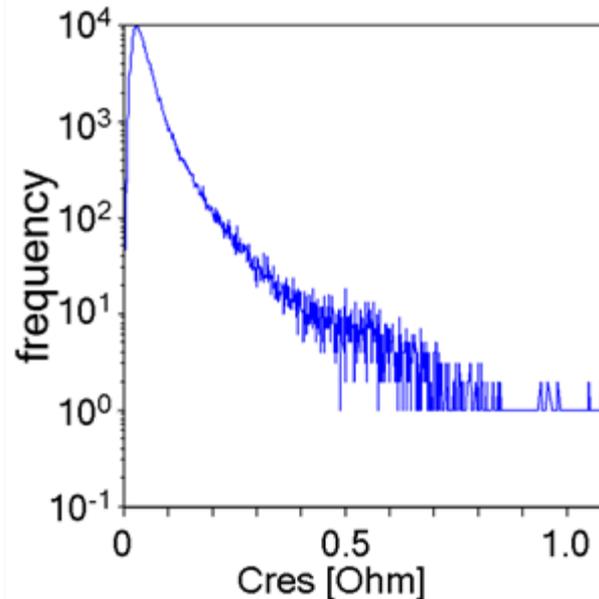
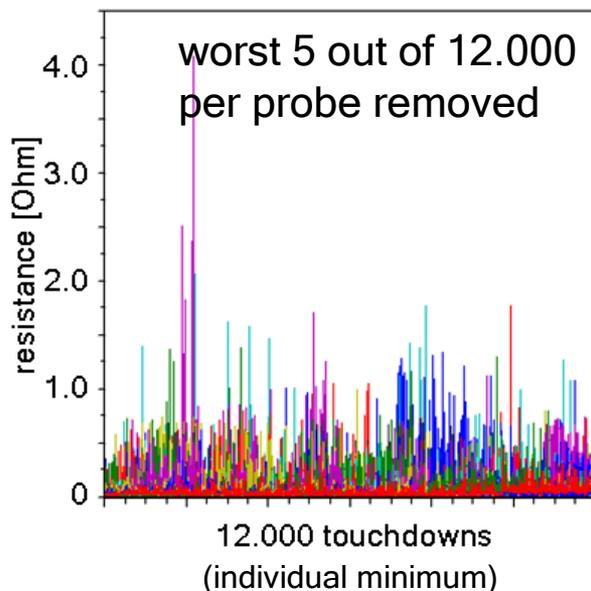
→ surface layer effects are visible

# 1 Copper Probing: summary

Copper probing is different from Al-probing:

- copper types are different
- same type can show a broad range of surface conditions

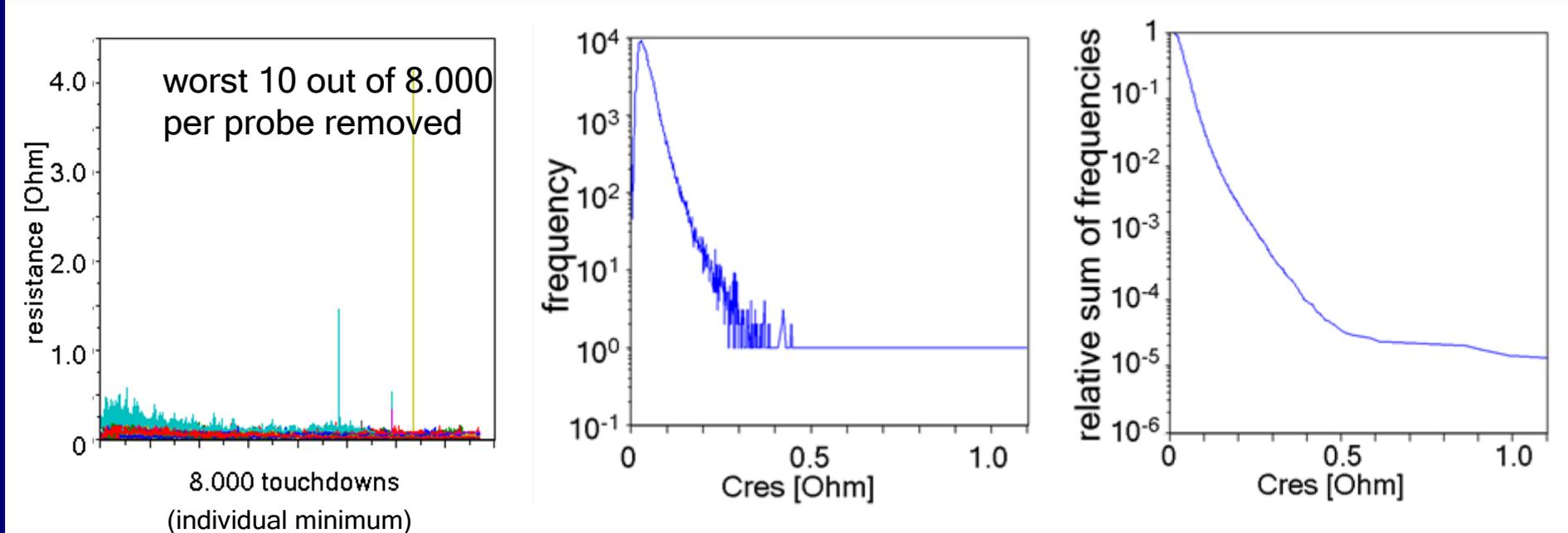
2.5mil probe on copper studs after application specific cleaning application



→ copper probing requires an application specific online cleaning for optimized Cres, lifetime and stability

## 2 Aluminum Probing: Cres

- 180°C probing
- still no cleaning at all

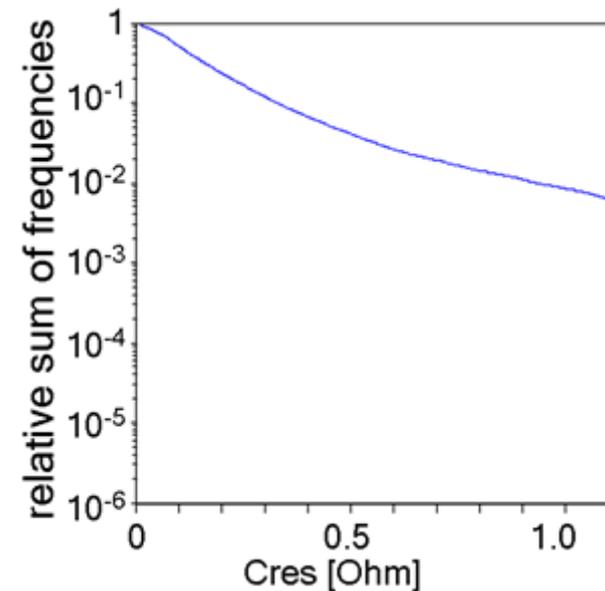
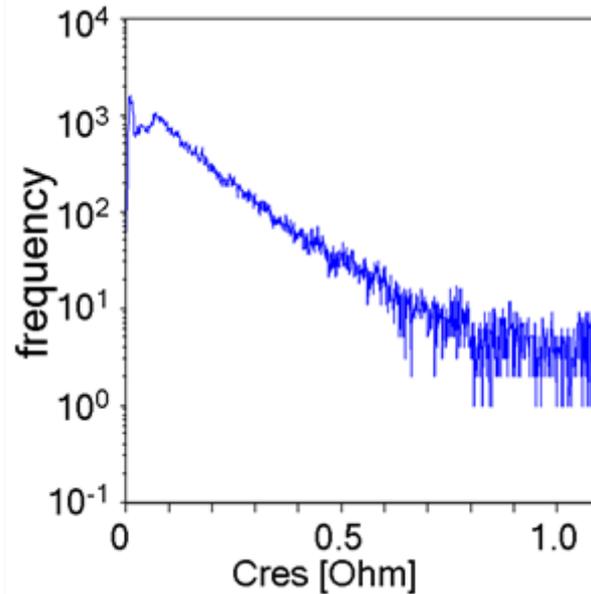
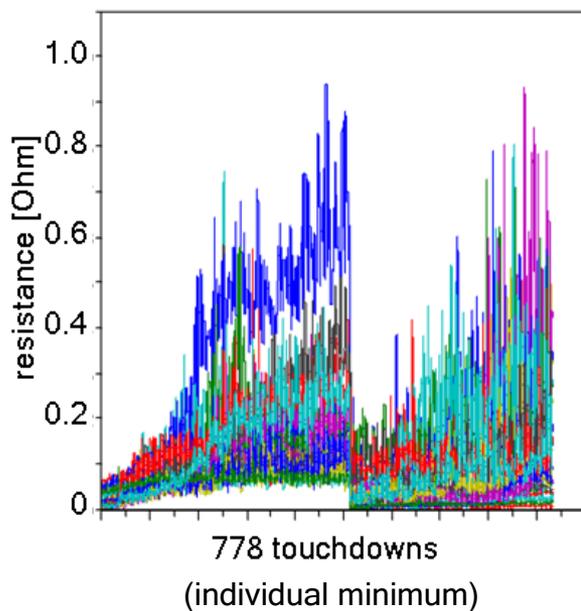


→ Very low Cres, even though the probes have been contaminated with copper

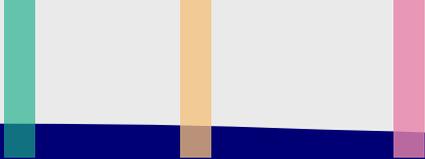
# Gold Probing:

## 3 Cres after Contamination with $\text{Cu}_x\text{O}_y$ and $\text{Al}_2\text{O}_3$

- I/U – measurements only
- best 36 probes out of 45



→ tip contamination leads to instable contacts, even on Gold

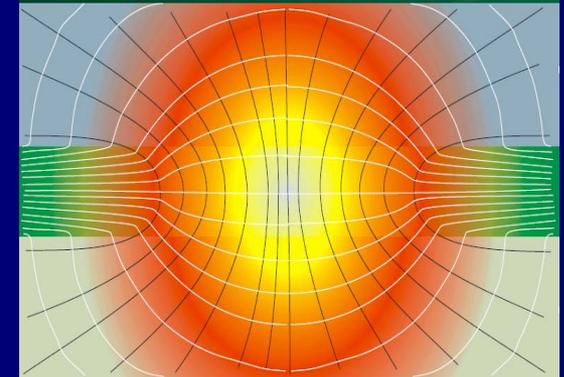


# Our Results

- Aluminum probing has been very stable, even under bad conditions
- Copper probing often requires application specific online cleaning
- Gold probing needs fresh tips

# Fritting Investigation

- Selected data from the I/U-measurements
- Fritting definition:  
 $R_{100\text{mA}} - R_{63\text{mA}} > 30\text{mOhm}$  Cres change

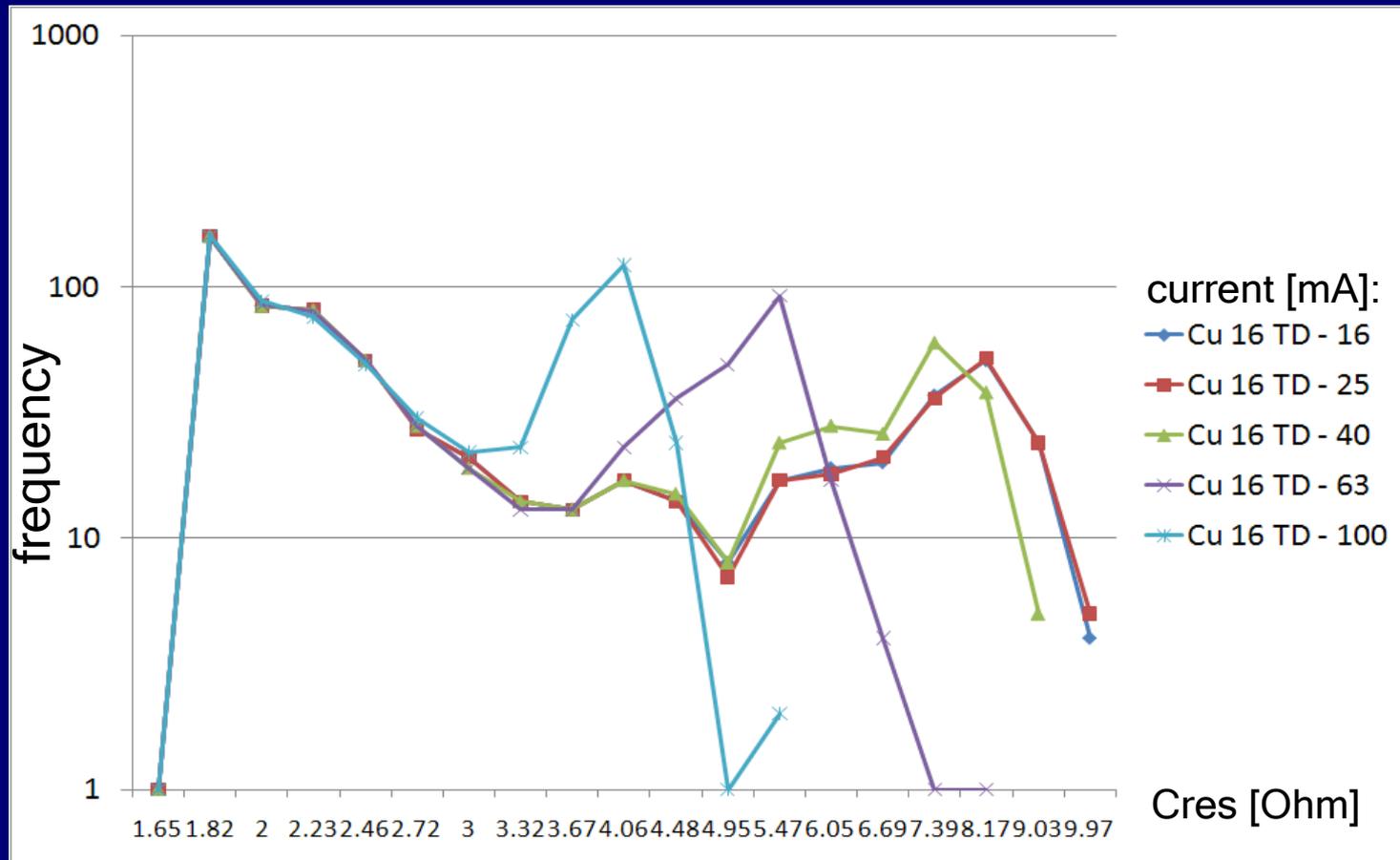


Available data sets so far:	percentage fritting contacts
- 50 TD on aluminum / 80μm OT .....	0.22%
- 16 TD on copper / 80 μm OT .....	36.16%
- 13 TD on aluminum / 80μm OT .....	1.37%
- 1 TD on copper / 13 sets of OT (20-80μm) .....	1.20%
- 1 TD on aluminum / 13 sets of OT (20-80μm) .....	1.71%
- 350 TD on gold / 80μm OT .....	3.54%

test order ↓

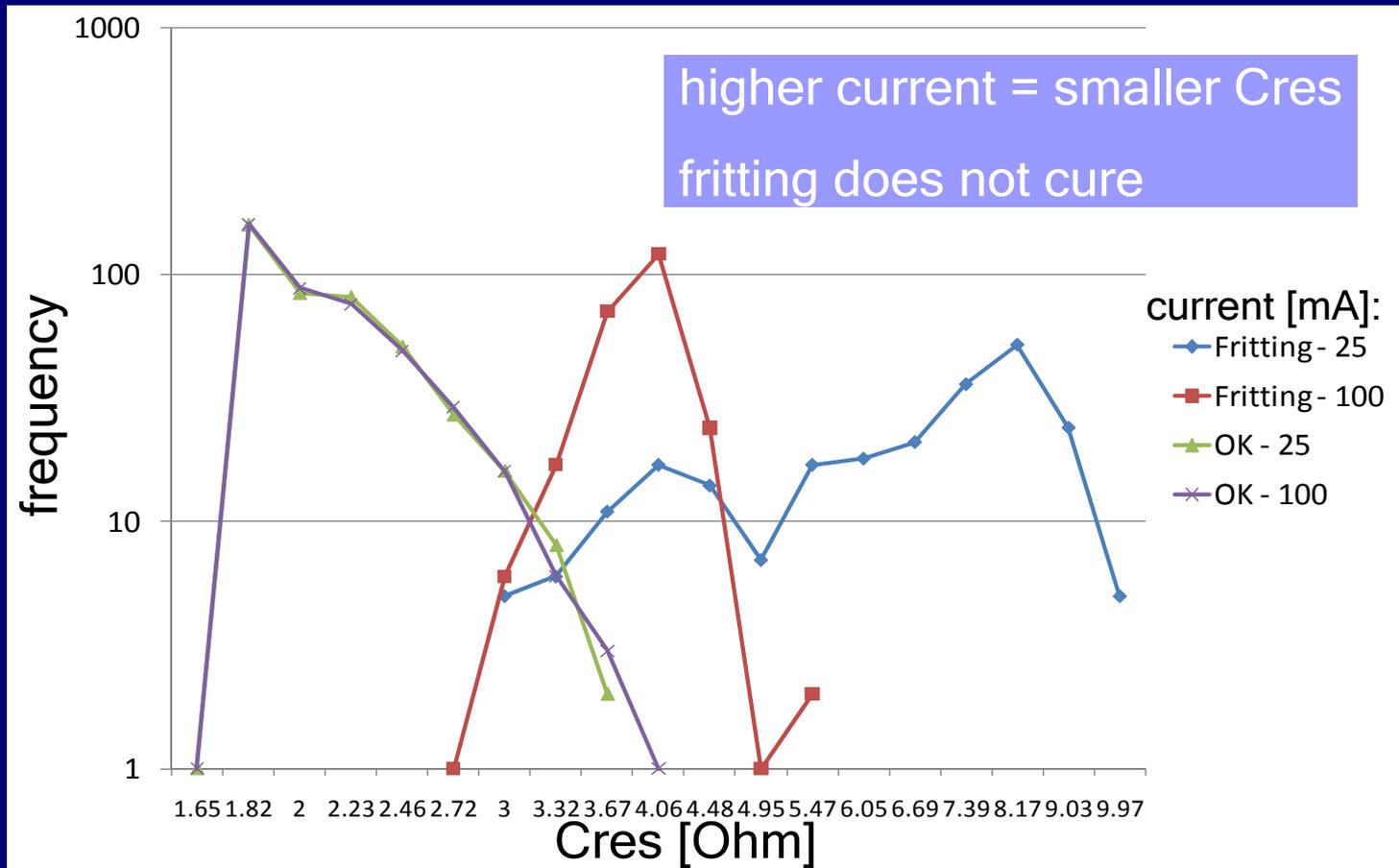
# Fritting on Copper

## 16 TD CRES distribution



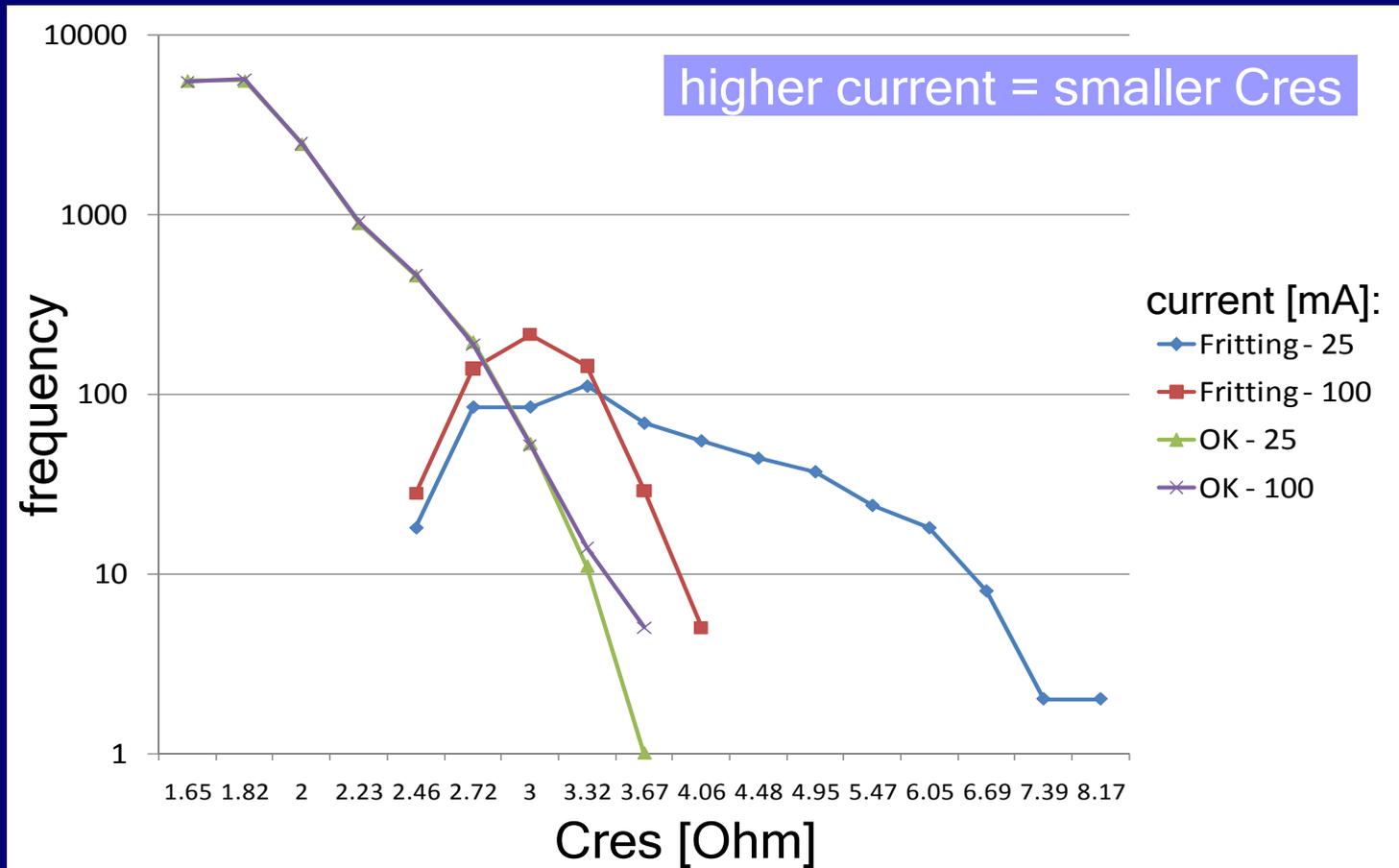
# Fritting on Copper

## 16 TD CRES distribution



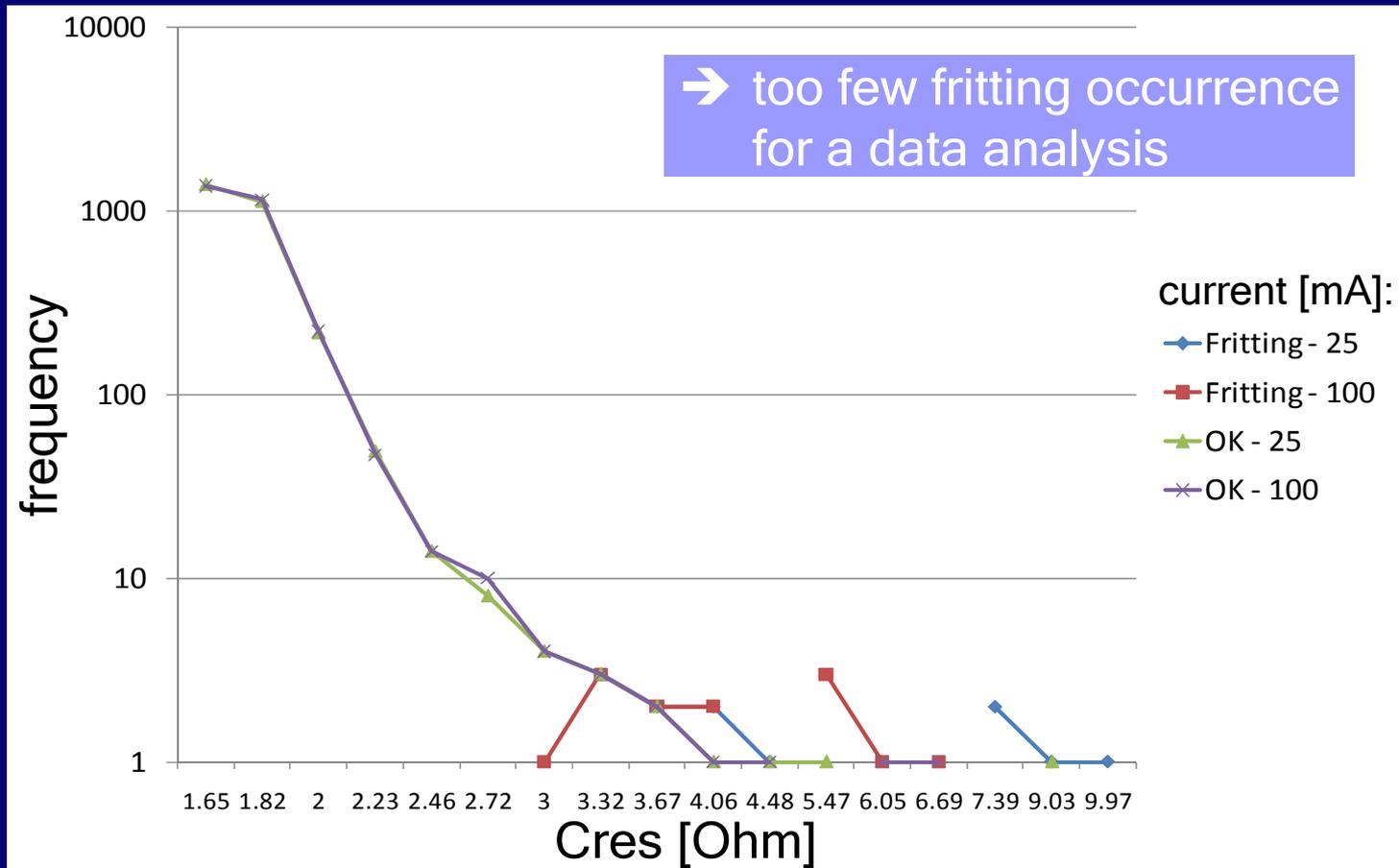
# Fritting on Gold after Contamination with $\text{Cu}_x\text{O}_y$ and $\text{Al}_2\text{O}_3$

350 TD CRES distribution

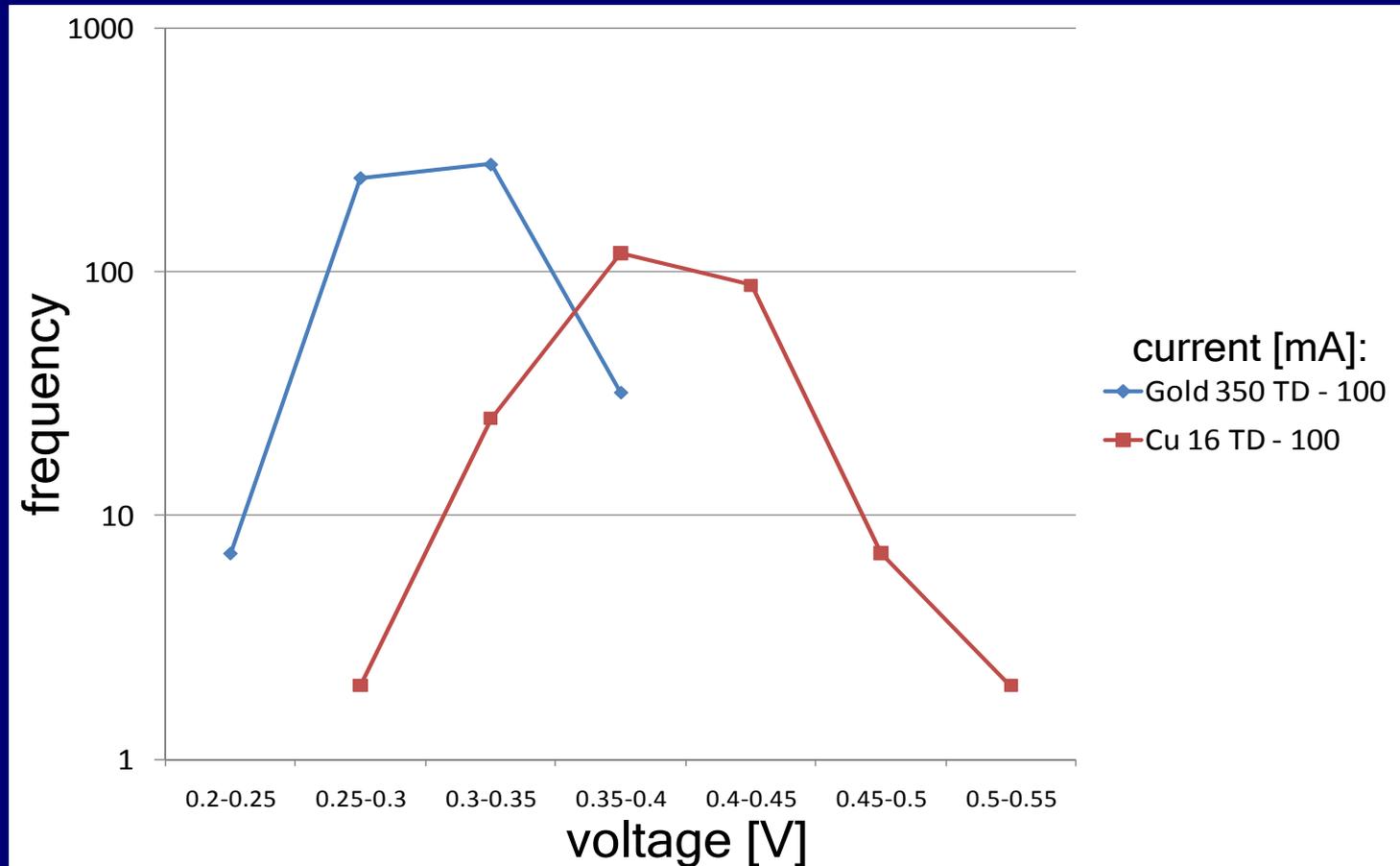


# Fritting on Aluminum

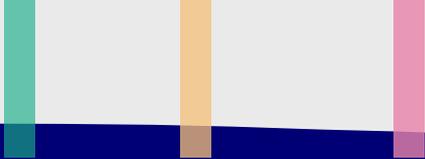
50+13 TD CRES distribution



# Fritting Voltage Distribution @ 100mA



→ indication towards material dependence of fritting voltage



# Our Results

- Fritting requires a specific minimum current and voltage.\*
- Higher current yields lower resistance.  
Fritting does not “heal” the contact.\*
- Fritting voltages may depend on pad materials.  
We found values from 0.2V to 0.5V.

\* see SWTW, MARTENS 2006 and 2009 and DEGEN 2006

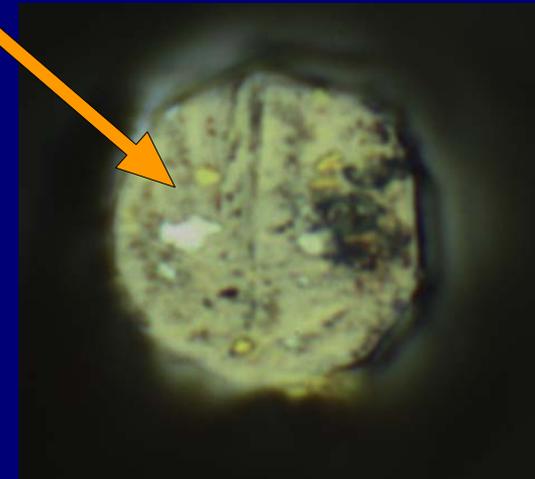
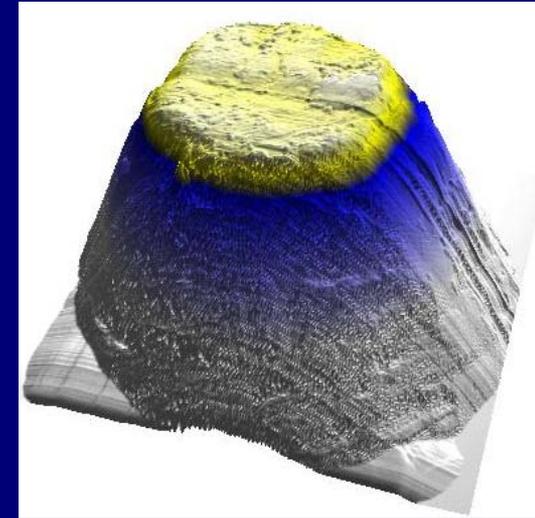
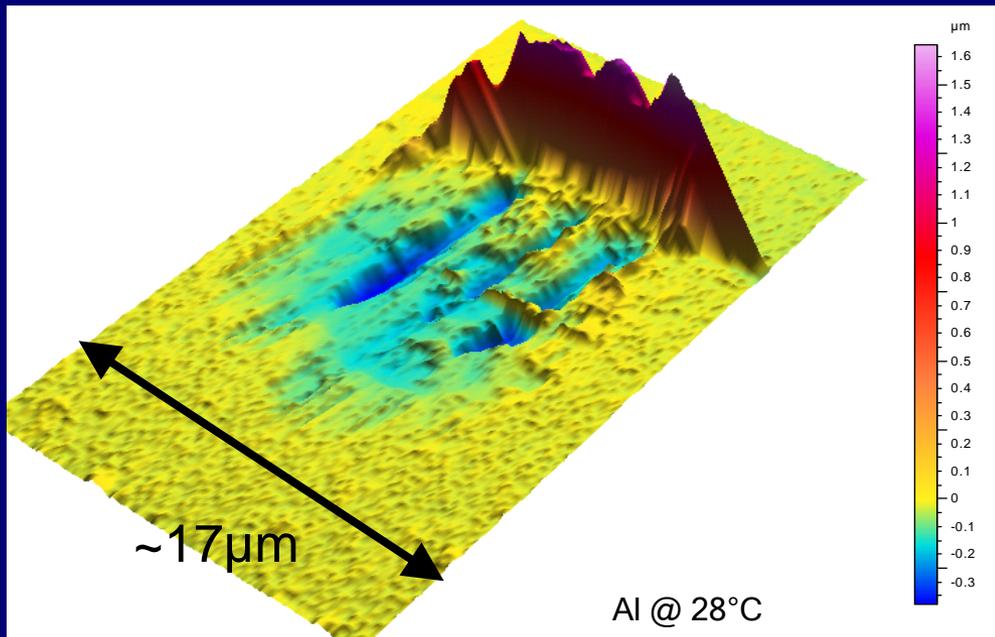
# AFM Measurements on Probe #25

## Probe Tip and Scrub Mark Topography

Beam after 26439 touchdowns

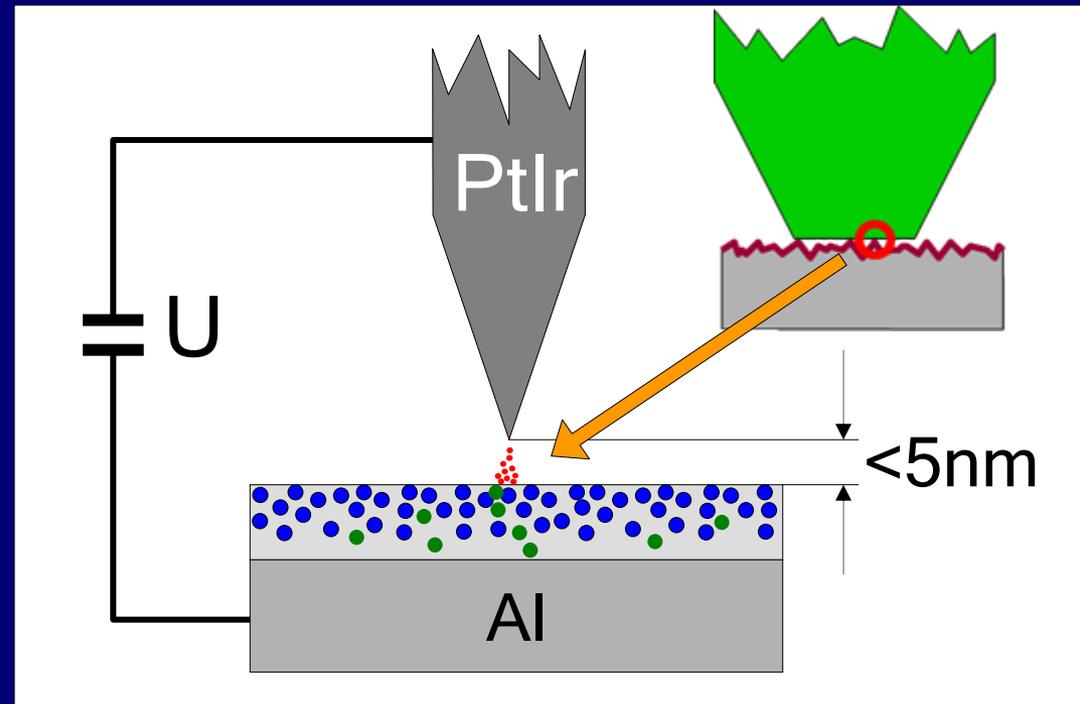
Diameter: 14  $\mu\text{m}$

Traces of all pad materials on surface



# Scanning Tunnel Spectroscopy

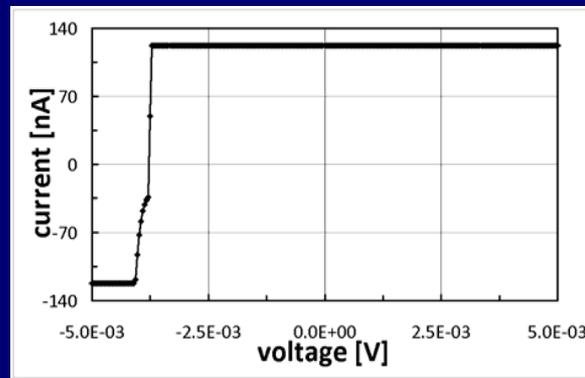
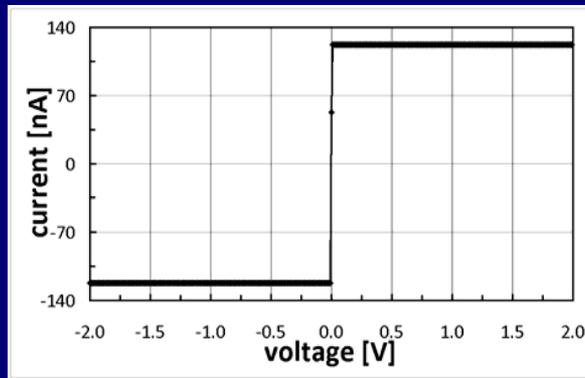
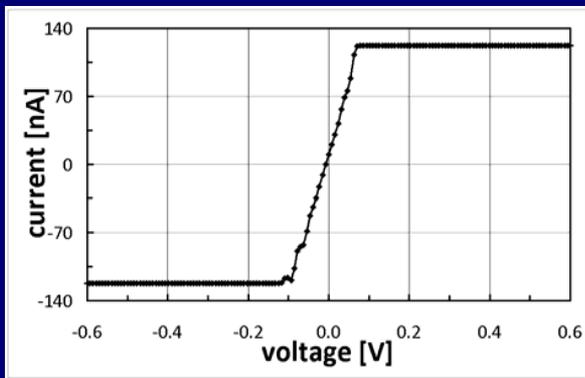
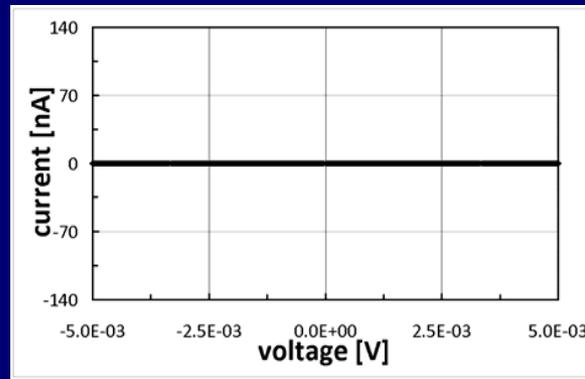
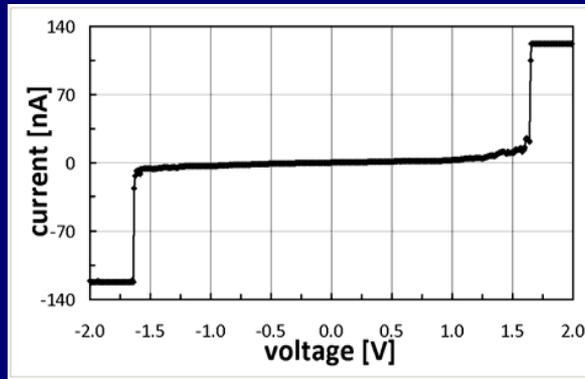
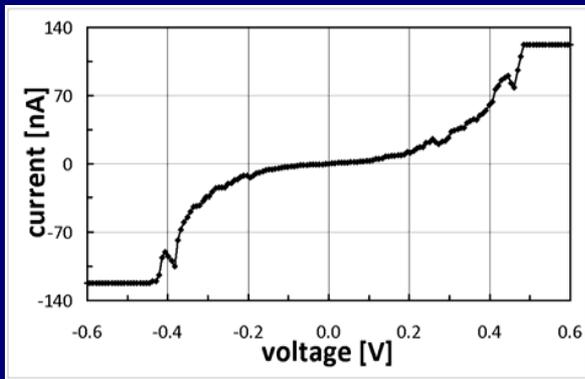
- Measuring the conductivity of a surface
- NO contact to the surface, but distance in the tunneling range
- extremely tight distance control



# Scanning Tunnel Spectroscopy

voltage dependent  
resistance

constant  
resistance



copper

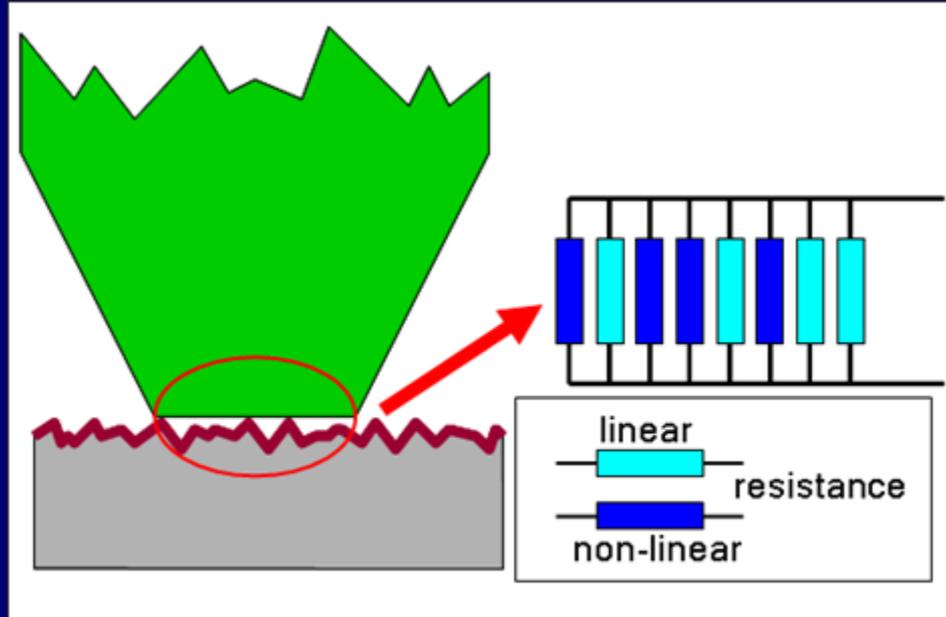
aluminum

gold

# Soft contacts for POAA

“No damage” contacts for POAA will rise the following challenges:

- more complex contact physics:
  - acceptable for logic I/O
  - critical for power/GND
  - difficult for analog signals
- non-linear contact characteristics

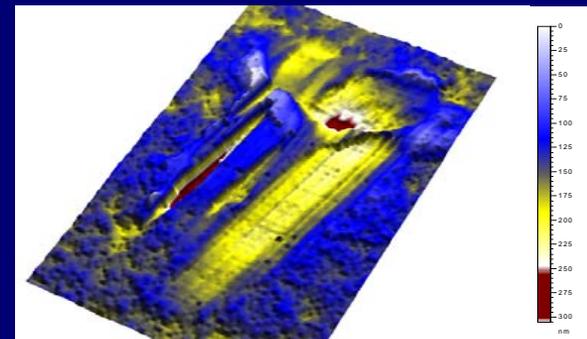
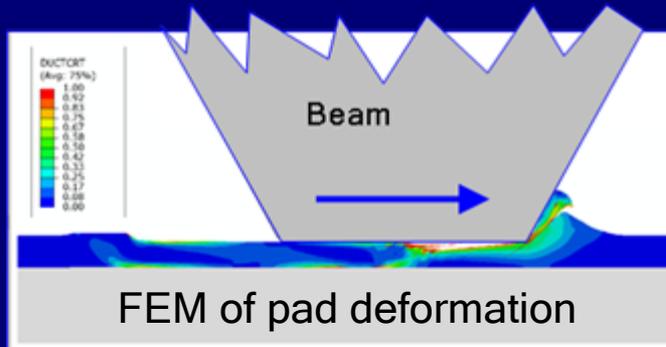


→ no real limit for measurements, but a challenge for power supply

# Advanced Contact Requirements are Covered by Simulations

To optimize a system the following components are required:

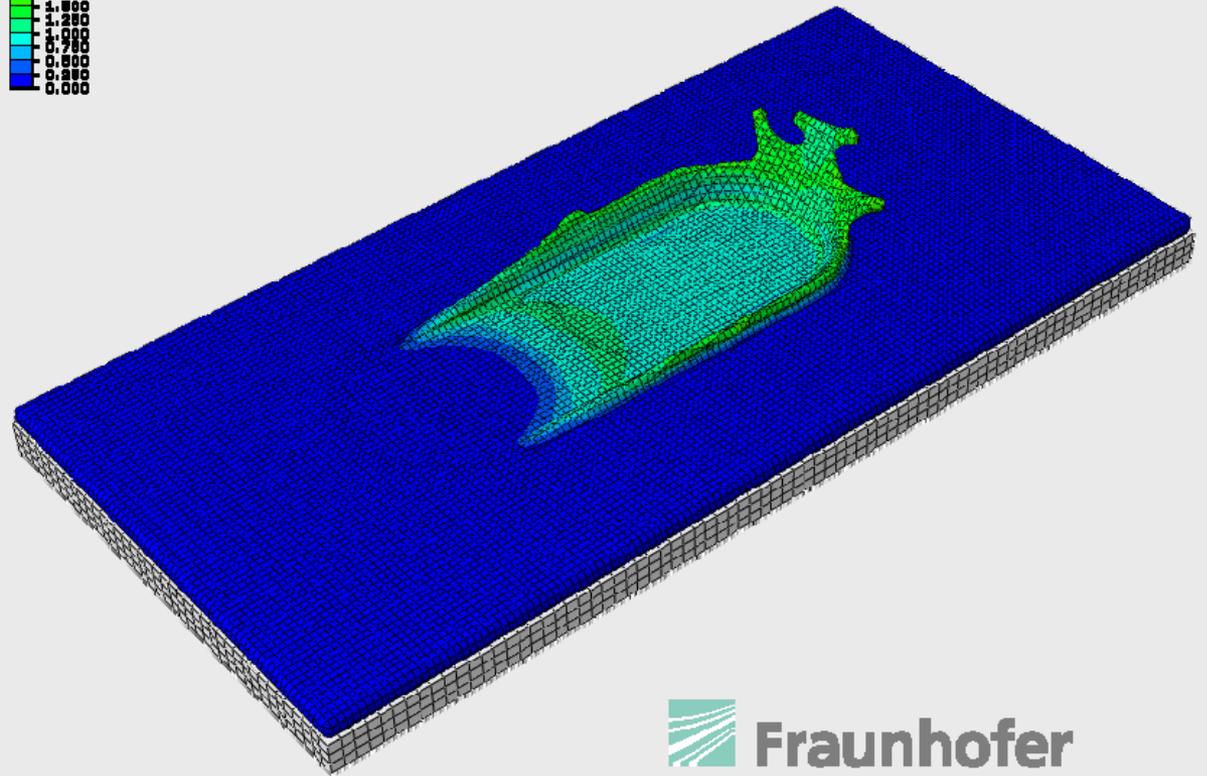
- Accurate measurements of scrub mark dimension and depth using AFM
- Measurements of the tip using AFM or SEM and microscope
- FEM simulation to correlate the theory to the experiment



# FEM simulation of probing Al with 1.6mil probe

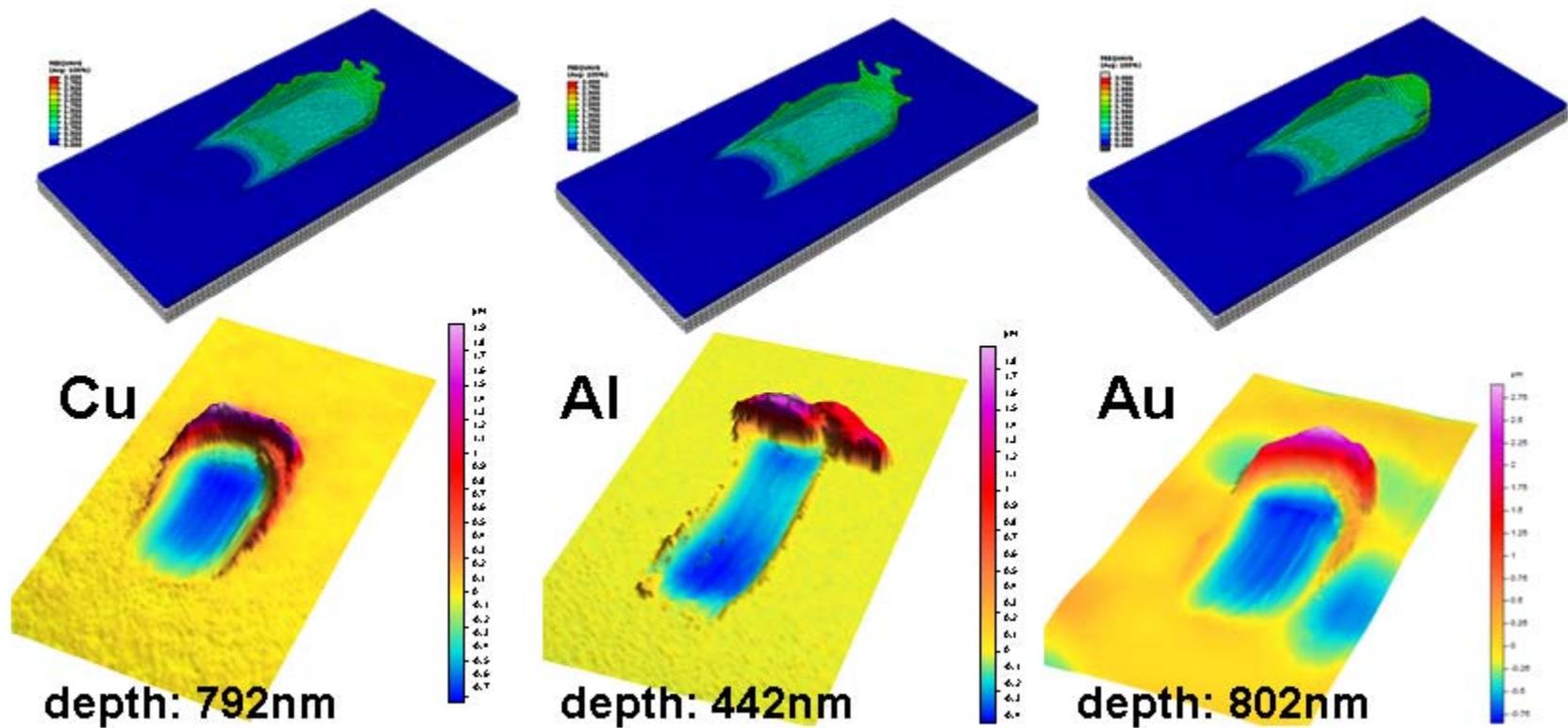
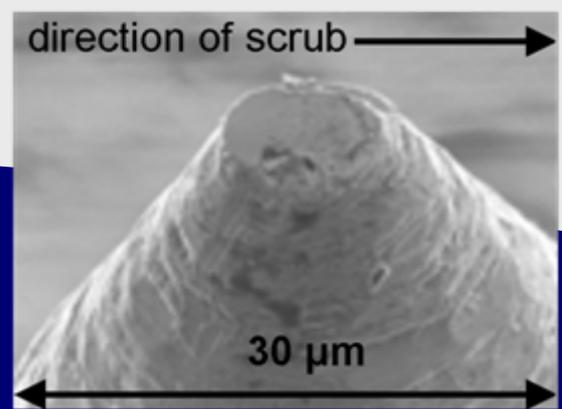
PEEQVAV8  
(Avg: 100%)

3.000
2.750
2.500
2.250
2.000
1.750
1.500
1.250
1.000
0.750
0.500
0.250
0.000

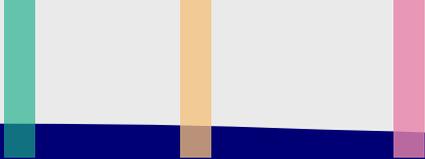


path controlled  
calculation

# Comparison of FEM and AFM Measurements

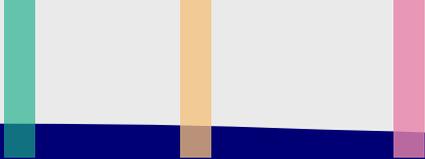


the probe above has been used for these scrubs



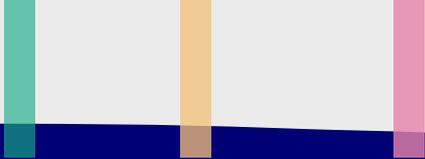
# Summary

- Common probing relies on surface deformation but leads to a contact with constant, small resistance
- “No damage” probing requires a more detailed test algorithm to take the contact interface into account.
- An optimized system allows for stable soft contacts. Optimization will include detailed surface analysis combined with extended simulation.
- Fritting can be predicted by initial resistance measurement.



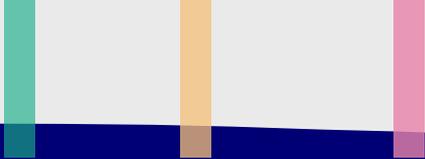
# Outlook

- Extending the experiments towards service life.
- Including very high current applications.
- Constantly enhance analytics for probes and pads.
- Develop simulations towards CAE/CAM for next generation probes.



# Acknowledgements

- Tino Stephan (Fraunhofer-IWM) - AFM measurements, film thickness
- Georg Lorenz (Fraunhofer-IWM) - FEM simulations
- Martin Bogner (Uni-Stuttgart) - STS measurements
- Juergen Bauersfeld (FEINMETALL) - prober tests, prober software
- Michael Holocher (FEINMETALL) - testhead preparation
- Georg Steidle (FEINMETALL) - AFM measurements
- Christoph Gers (FEINMETALL) - contact technology



# Thank You.

**FEINMETALL GmbH**  
**Herrenberg, Germany**  
**[www.feinmetall.de](http://www.feinmetall.de)**